

# **BGA6289**

# MMIC wideband medium power amplifier

Rev. 02 — 15 June 2009

**Product data sheet** 

## 1. Product profile

## 1.1 General description

The BGA6289 is a silicon Monolithic Microwave Integrated Circuit (MMIC) wideband medium power amplifier with internal matching circuit in a 3-pin SOT89 plastic low thermal resistance SMD package.

The BGA6x89 series of medium power gain blocks are resistive feedback Darlington configured amplifiers. Resistive feedback provides large bandwidth with high accuracy.

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

#### 1.2 Features

- Broadband 50 Ω gain block
- 17 dBm power output
- SOT89 package
- Single supply voltage needed

## 1.3 Applications

- Broadband medium power gain blocks
- Small signal high linearity amplifiers
- Variable gain and high output power in combination with the BGA2031
- Cellular, PCS and CDPD
- IF/RF buffer amplifier
- Wireless data SONET
- Oscillator amplifier, final PA
- Drivers for CATV amplifier



## MMIC wideband medium power amplifier

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_D$	DC device voltage	on pin 1; $I_S = 88 \text{ mA}$	-	4.1	-	V
I <sub>S</sub>	DC supply current	$V_S$ = 8 V; $R_{bias}$ = 47 $\Omega$ ; $T_j$ = 25 °C	-	88	-	mA
$ s_{21} ^2$	insertion power gain	f = 1.95 GHz	-	13	-	dB
NF	noise figure	f = 1.95 GHz	-	4	-	dB
LIGD	input power at 1 dB gain compression	f = 850 MHz	-	18	-	dBm
		f = 1.95 GHz	-	16	-	dBm

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	RF_OUT/BIAS		
2	GND		2
3	RF_IN	3 2 1	3 12 /// sym130

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BGA6289	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BGA6289	3A

### **MMIC** wideband medium power amplifier

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_D$	DC device voltage	on pin 1; RF input AC coupled	-	6.0	V
I <sub>S</sub>	DC supply current		-	150	mΑ
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 70 °C	<u>[1]</u> _	800	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
$P_D$	drive power		-	15	dBm

<sup>[1]</sup>  $T_{sp}$  is the temperature at the solder point of ground lead, pin 2.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$T_{sp} \le 70~^{\circ}C$	<u>[1]</u> 100	K/W

<sup>[1]</sup>  $T_{sp}$  is the temperature at the solder point of ground lead, pin 2.

## 7. Characteristics

Table 7. Static characteristics

 $V_S = 8 \ V; \ T_j = 25 \ ^{\circ}C; \ R_{bias} = 47 \ \Omega^{[1]}$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_D$	DC device voltage	on pin 1; $I_S = 88 \text{ mA}$	-	4.1	-	V
Is	DC supply current		79	88	96	mA

<sup>[1]</sup>  $V_S = DC$  operating supply voltage applied to  $R_{bias}$ ; see Figure 10

#### Table 8. Characteristics

 $V_S$  = 8 V;  $I_S$  = 88 mA;  $T_{amb}$  = 25  $^{\circ}$  C;  $R_{bias}$  = 47  $\Omega$ ;  $IP3_{(out)}$  tone spacing = 1 MHz;  $P_L$  = 0 dBm per tone;  $Z_L$  =  $Z_S$  = 50  $\Omega$ ; unless otherwise specified; see <u>Figure 10</u>.

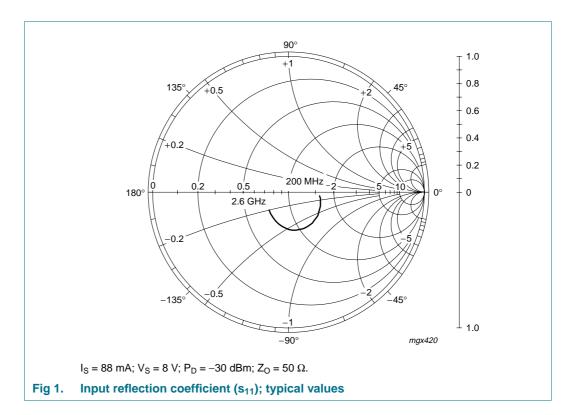
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ s_{21} ^2$	insertion power gain	f = 850 MHz	-	15	-	dB
		f = 1.95 GHz	-	13	-	dB
		f = 2.5 GHz	-	12	-	dB
$R_{LIN}$	input return loss	f = 850 MHz	-	11	-	dB
		f = 1.95 GHz	-	11	-	dB
		f = 2.5 GHz	-	14	-	dB
$R_{LOUT}$	output return loss	f = 850 MHz	-	11	-	dB
		f = 1.95 GHz	-	14	-	dB
		f = 2.5 GHz	-	14	-	dB

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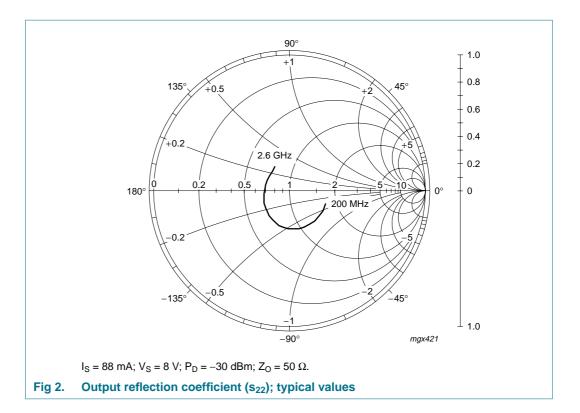
## MMIC wideband medium power amplifier

**Table 8.** Characteristics ...continued  $V_S = 8 \ V$ ;  $I_S = 88 \ mA$ ;  $T_{amb} = 25 \ ^{\circ}C$ ;  $R_{bias} = 47 \ \Omega$ ;  $IP3_{(out)}$  tone spacing = 1 MHz;  $P_L = 0 \ dBm$  per tone;  $Z_L = Z_S = 50 \ \Omega$ ; unless otherwise specified; see <u>Figure 10</u>.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure	f = 850 MHz	-	3.5	-	dB
		f = 1.95 GHz	-	3.7	-	dB
		f = 2.5 GHz	-	3.8	-	dB
K	stability factor	f = 850 MHz	-	1.3	-	
		f = 2.5 GHz	-	1.6	-	
$P_{L1dB}$	output power at 1 dB	f = 850 MHz	-	17	-	dBm
	gain compression	f = 1.95 GHz	-	15	-	dBm
IP3 <sub>(in)</sub>	input intercept point	f = 850 MHz	-	17	-	dBm
		f = 2.5 GHz	-	14	-	dBm
IP3 <sub>(out)</sub>	output intercept point	f = 850 MHz	-	31	-	dBm
		f = 2.5 GHz	-	25	-	dBm



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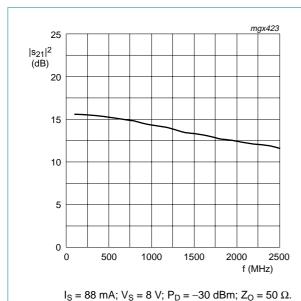
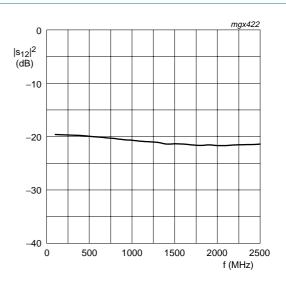


Fig 3. Insertion gain  $(|s_{21}|^2)$  as a function of frequency; typical values



 $I_S$  = 88 mA;  $V_S$  = 8 V;  $P_D$  = –30 dBm;  $Z_O$  = 50  $\Omega.$ 

Fig 4. Isolation  $(|s_{12}|^2)$  as a function of frequency; typical values

### MMIC wideband medium power amplifier

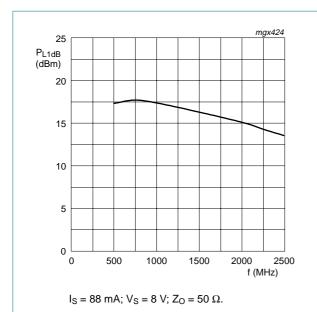
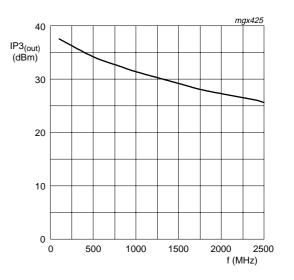


Fig 5. Load power as a function of frequency; typical values



 $I_S$  = 88 mA;  $V_S$  = 8 V;  $P_L$  = 0 dBm;  $Z_O$  = 50  $\Omega.$ 

Fig 6. Output intercept point as a function of frequency; typical values

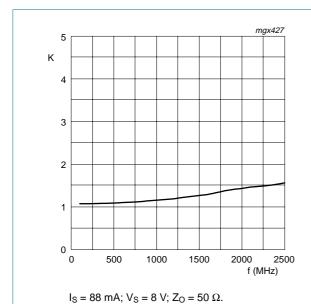
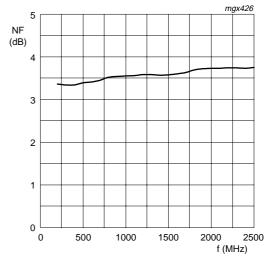


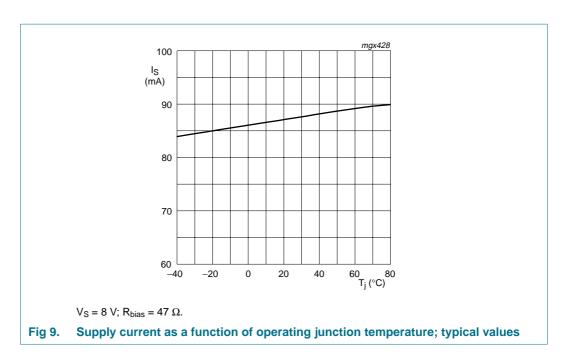
Fig 7. Stability factor as a function of frequency; typical values



 $I_S$  = 88 mA;  $V_S$  = 8 V;  $Z_O$  = 50  $\Omega.$ 

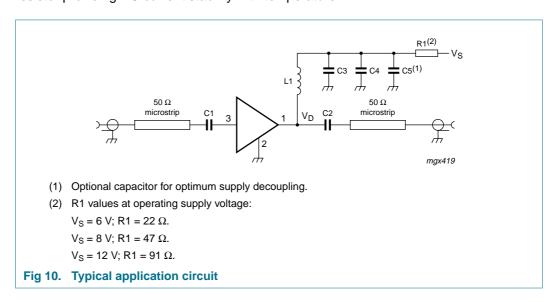
Fig 8. Noise figure as a function of frequency; typical values

#### MMIC wideband medium power amplifier



## 8. Application information

Figure 10 shows a typical application circuit for the BGA6289 MMIC. The device is internally matched to 50  $\Omega$ , and therefore does not require any external matching. The value of the input and output DC blocking capacitors C1 and C2 depends on the operating frequency; see Table 9. Capacitors C1 and C2 are used in conjunction with L1 and C3 to fine tune the input and output impedance. Capacitor C4 is a supply decoupling capacitor. A 1 μF capacitor (C5) can be added for optimum supply decoupling. The external components should be placed as close as possible to the MMIC. When using via holes, use multiple via holes per pin in order to limit ground path induction. Resistor R1 is a bias resistor providing DC current stability with temperature.



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Table 9. List of components

See Figure 10 for circuit.

Component	Description	Package	Value at operating frequency				
			500 MHz	800 MHz	1950 MHz	2400 MHz	3500 MHz
C1, C2	multilayer ceramic chip capacitor	0603	220 pF	100 pF	68 pF	56 pF	39 pF
C3	multilayer ceramic chip capacitor	0603	100 pF	68 pF	22 pF	22 pF	15 pF
C4	multilayer ceramic chip capacitor	0603	1 nF	1 nF	1 nF	1 nF	1 nF
C5[1]	electrolytic or tantalum capacitor	0603	1 μF	1 μF	1 μF	1 μF	1 μF
L1	SMD inductor	0603	68 nH	33 nH	22 nH	18 nH	15 nH
R1	SMD resistor 0.5 W; $V_S = 8 \text{ V}$	-	$47~\Omega$	$47~\Omega$	47 Ω	47 Ω	47 Ω

<sup>[1]</sup> Optional.

## Table 10. Scattering parameters

 $I_S = 88 \text{ mA}; V_S = 8 \text{ V}; P_D = -30 \text{ dBm}; Z_O = 50 \Omega; T_{amb} = 25 \,^{\circ}\text{C}.$ 

f (MHz)	s <sub>11</sub>		s <sub>21</sub>	s <sub>21</sub>		S <sub>12</sub>			K
	Magnitude (ratio)	Angle (degree)							
800	0.327	-33.05	5.49	134.89	0.10	-11.30	0.29	-76.80	1.2
1000	0.28	-42.87	5.20	124.72	0.09	-12.71	0.28	-92.51	1.2
1200	0.29	-52.85	5.00	115.06	0.09	-13.51	0.27	-107.2	1.3
1400	0.29	-62.55	4.69	105.73	0.09	-13.66	0.25	-121.6	1.4
1600	0.29	-73.03	4.55	97.33	0.09	-13.18	0.23	-136.8	1.4
1800	0.28	-83.21	4.31	88.55	0.08	-12.17	0.21	-153.4	1.5
2000	0.26	-94.25	4.18	80.63	0.08	-12.11	0.19	-172.3	1.5
2200	0.24	-106.7	4.02	72.01	0.08	-10.45	0.18	166.36	1.5
2400	0.22	-120.4	3.91	63.83	0.08	-10.70	0.18	144.2	1.6
2600	0.19	-137.7	3.71	55.62	0.09	-10.65	0.20	122.13	1.2

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## 9. Package outline

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89

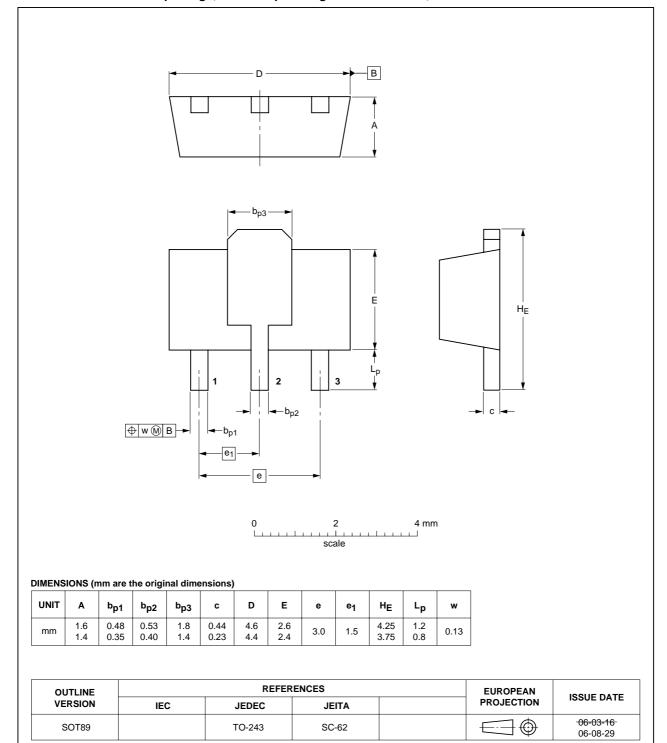


Fig 11. Package outline SOT89 (SC-62)

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## **MMIC** wideband medium power amplifier

## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDPD	Cellular Digital Packet Data
IF	Intermediate Frequency
PCS	Personal Communication Service
SMD	Surface Mount Device
SONET	Synchronous Optical NETwork

# 11. Revision history

Table 12. Revision history

Release date	Data sheet status	Change notice	Supersedes	
20090615	Product data sheet	-	BGA6289_1	
<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
<ul> <li>Changed I<sub>S</sub> from 84 mA to 88 mA throughout.</li> </ul>				
<ul> <li>Table 1: changed symbol V<sub>S</sub> to V<sub>D</sub>.</li> </ul>				
• Table 5: changed symbol V <sub>S</sub> to V <sub>D</sub> and added "on pin 1;" to Conditions.				
Table 7: added row for V <sub>D</sub> DC device voltage.				
Section 8: added sentence.				
• Figure 10: figure notes modified.				
• Table 9: changed $V_S = 9 \text{ V to } 8 \text{ V}$ .				
• Table 9: added 47 Ω to all value columns for resistor R1 and amended values of C3 and C4.				
20030918	Product data sheet	-	-	
	20090615  The format of guidelines of Legal texts has Changed Is 1 Table 1: charant ch	<ul> <li>The format of this data sheet has been guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new Changed I<sub>S</sub> from 84 mA to 88 mA throuten Table 1: changed symbol V<sub>S</sub> to V<sub>D</sub>.</li> <li>Table 5: changed symbol V<sub>S</sub> to V<sub>D</sub> and Table 7: added row for V<sub>D</sub> DC device vores Section 8: added sentence.</li> <li>Figure 10: figure notes modified.</li> <li>Table 9: changed V<sub>S</sub> = 9 V to 8 V.</li> <li>Table 9: added 47 Ω to all value columnations.</li> </ul>	<ul> <li>The format of this data sheet as been redesigned to comply we guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where the changed I<sub>S</sub> from 84 mA to 88 mA throughout.</li> <li>Table 1: changed symbol V<sub>S</sub> to V<sub>D</sub>.</li> <li>Table 5: changed symbol V<sub>S</sub> to V<sub>D</sub> and added "on pin 1;" to Company to Company name where the changed symbol V<sub>S</sub> to V<sub>D</sub>.</li> <li>Table 7: added row for V<sub>D</sub> DC device voltage.</li> <li>Section 8: added sentence.</li> <li>Figure 10: figure notes modified.</li> <li>Table 9: changed V<sub>S</sub> = 9 V to 8 V.</li> <li>Table 9: added 47 Ω to all value columns for resistor R1 and an added to company the company to company the columns for resistor R1 and an added to company the columns for resistor R1 and an added to company the columns for resistor R1 and an added to company the columns for resistor R1 and an added to the new company name where the company the columns for resistor R1 and an added to the new company name where the company the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and an added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the new company name where the columns for resistor R1 and added to the columns for resistor R1</li></ul>	

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## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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